

Fig. 1a

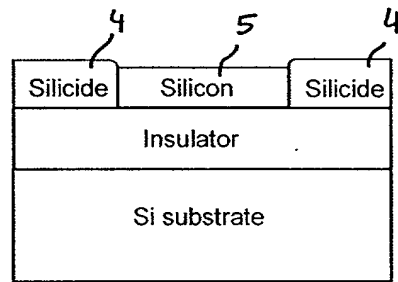


Fig. 1b

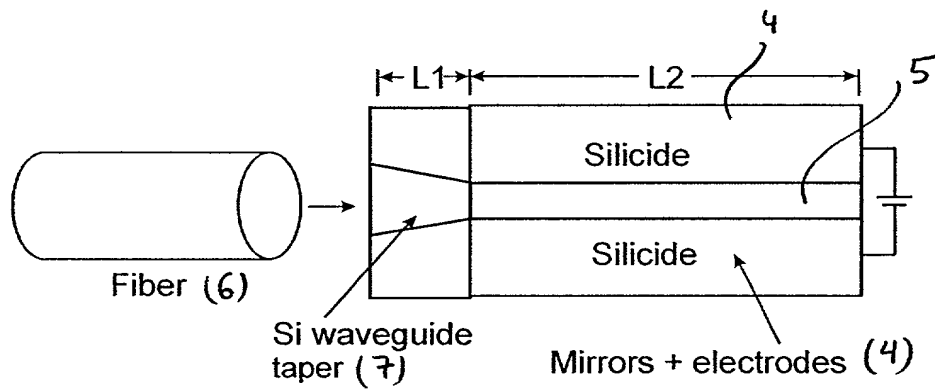


Fig. 1c

FIG. 2a is a cross-sectional view of a semiconductor device in accordance with the present invention, showing a Si substrate, an insulator, a silicon layer, a metal layer, a photoresist layer, and an oxide layer.

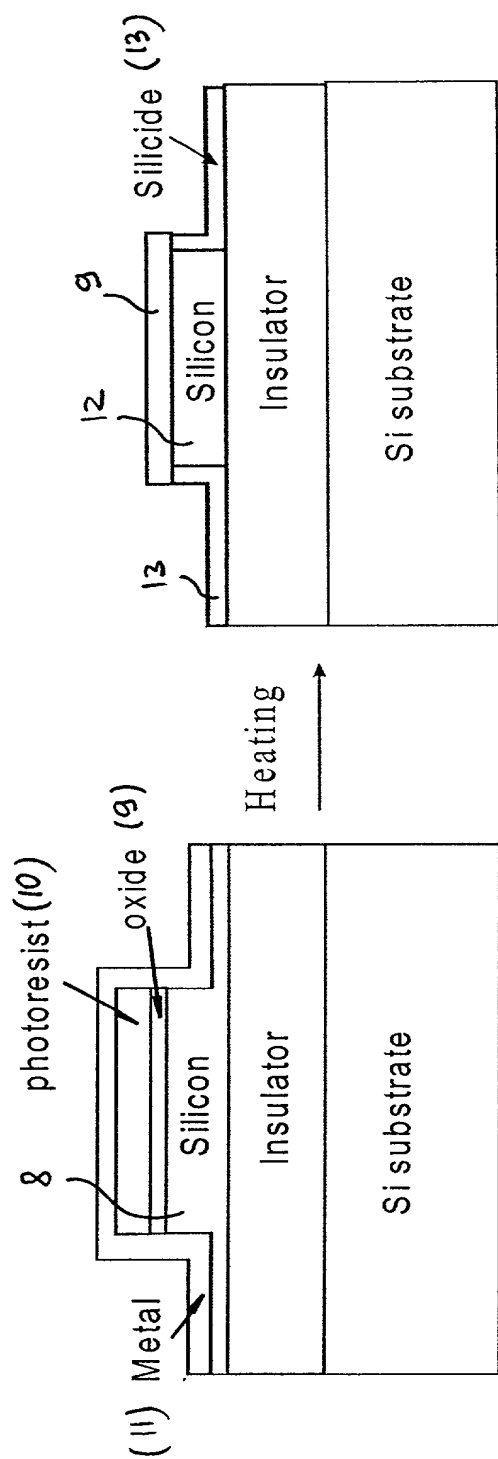


Fig. 2a

Fig. 2b

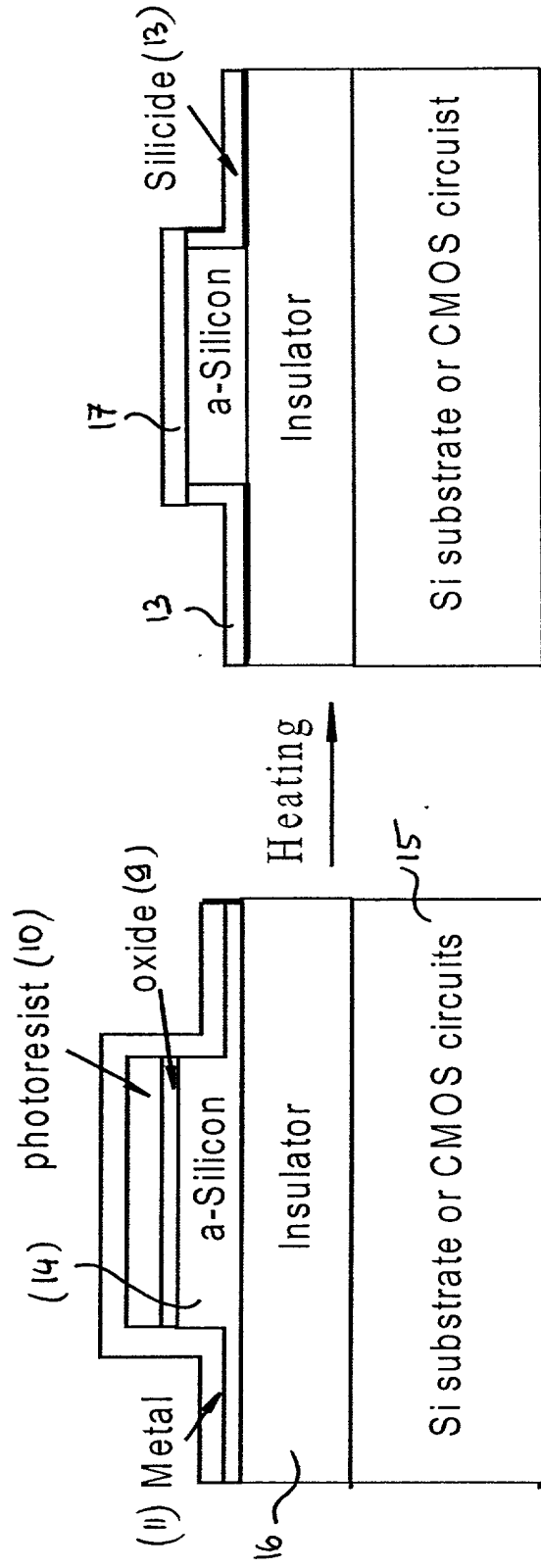


Fig. 3a

Fig. 3b

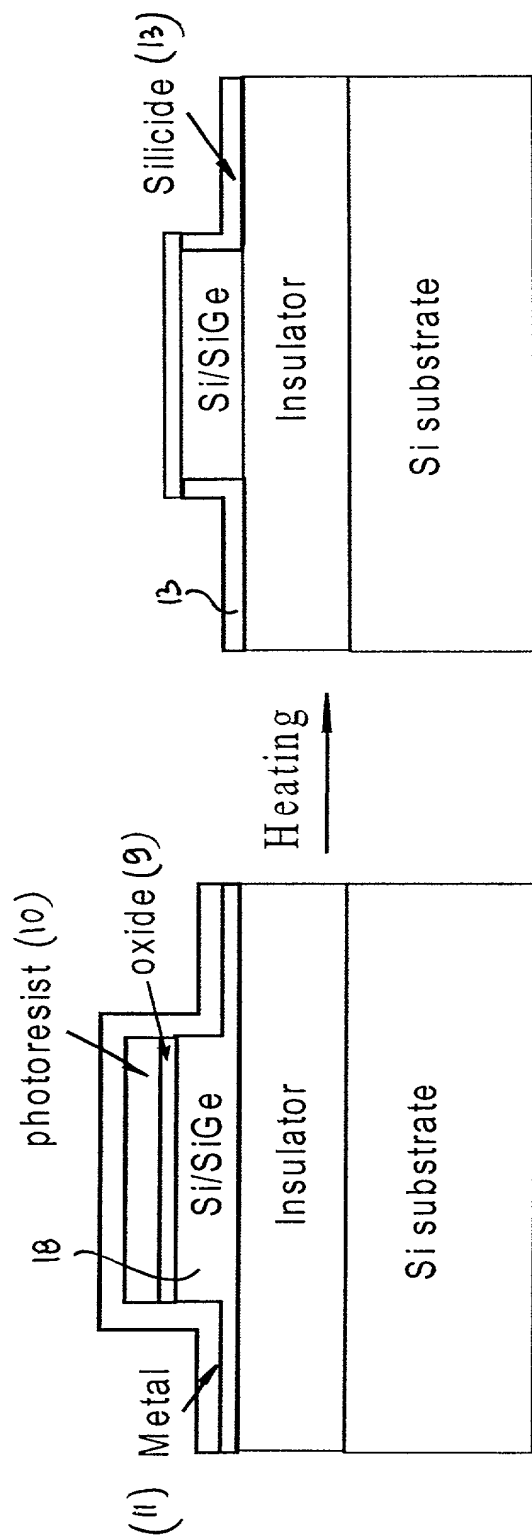


Fig. 4a

Fig. 4b

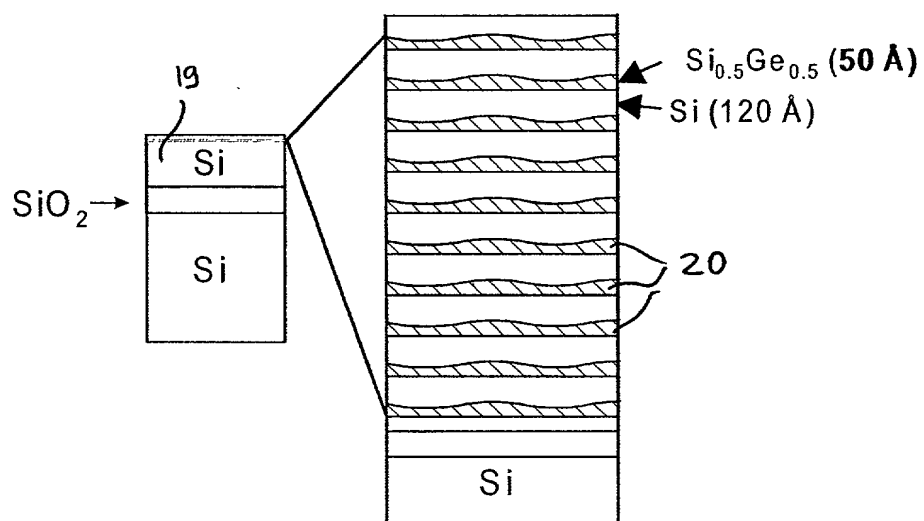


Fig. 5

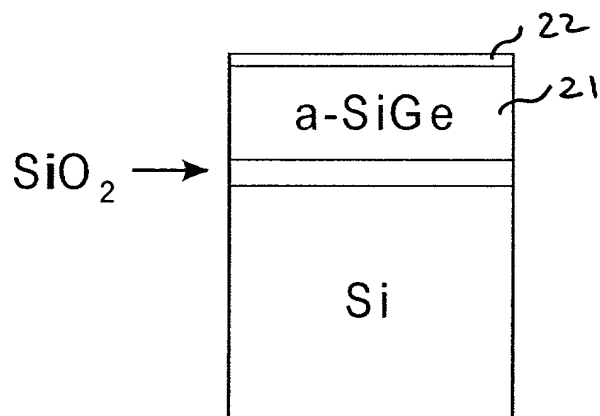


Fig. 6